



### MICROWAVE POWER GAN HEMT

# TGI7785-130LH

# MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### ·BROAD BAND INTERNALLY MATCHED HEMT

·HIGH POWER

**FEATURES** 

Pout= 51.0dBm at Pin= 44.0dBm

·HIGH GAIN

GL= 11.5dB at Pin= 20.0dBm

**-LOW INTERMODULATION DISTORTION** 

IM3(Min.)= -25dBc at Pout= 44.0dBm Single Carrier Level

·HERMETICALLY SEALED PACKAGE



## RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 40V IDSset= 0.8A f = 7.7 to 8.5GHz @Pin= 44dBm	dBm	50.0	51.0	_
Drain Current	IDS1		Α	_	7.0	9.0
Power Added Efficiency	ηadd		%	_	36	_
Linear Gain	GL	@Pin= 20dBm	dB	10.5	11.5	_
Gain flatness	ΔG		dB	_	_	±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 44.0dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-25	-30	_
Drain Current	IDS2		Α	_	_	5.0
Channel Temperature Rise *1	∆Tch		°C	_	120	140

### Recommended Gate Resistance(Rg): 28 $\Omega$

# ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 30mA	V	-2.0	-3.0	-5.0
Gate-Source Breakdown Voltage	VGSO	IGS= -25mA	٧	-10		_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	0.8	1.0

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- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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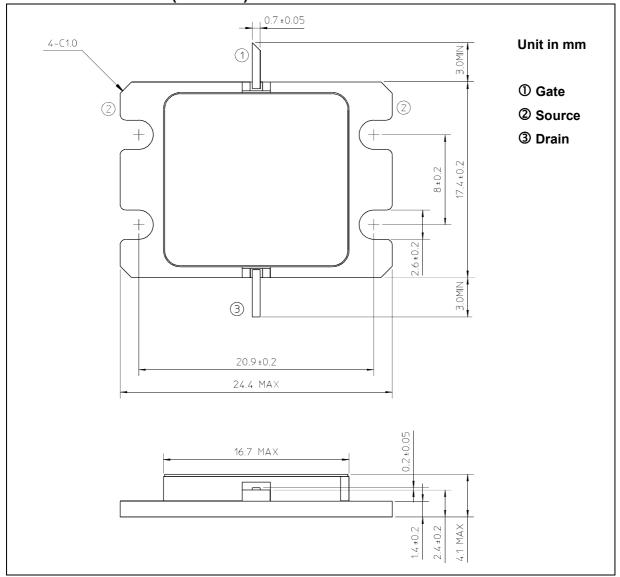
<sup>\*1:</sup>  $\Delta$ Tch = (VDS × IDS + Pin(two-tone) – Po(two-tone)) × Rth(c-c) It is calculated using the same condition as IM3 test.



## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	12
Total Power Dissipation (Tc= 25°C)	PT	W	200
Channel Temperature	Tch	°C	225
Storage Temperature	Tstg	°C	-65 to +175

## **PACKAGE OUTLINE (7-AA06A)**



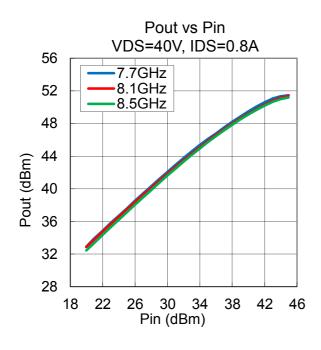
## HANDLING PRECAUTIONS FOR PACKAGE MODEL

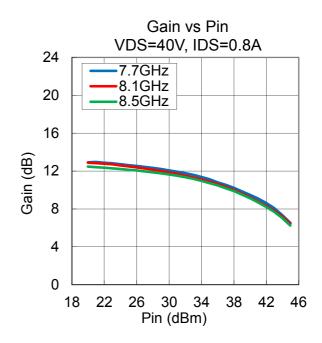
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C

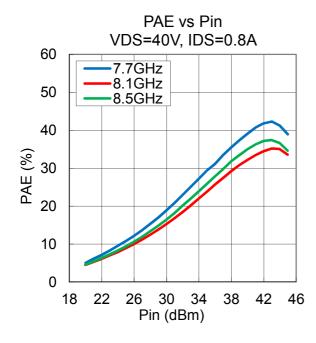
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

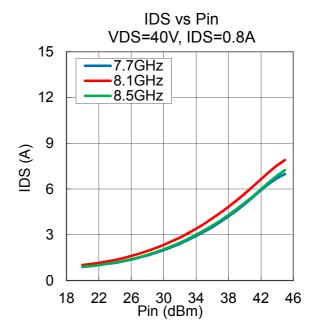
#### ·Pout, Gain, PAE, IDS vs. Pin

VDS= 40 V, IDSset= 0.8 A, f= 7.7, 8.1, 8.5 GHz, Ta= +25 °C





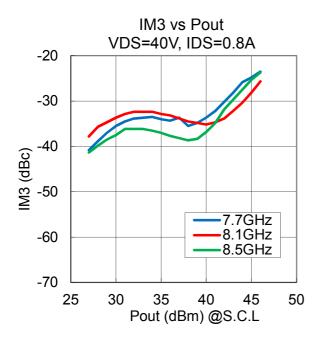


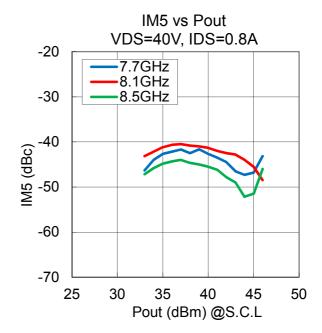


MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### ·IM3, IM5 vs. Pout

VDS= 40 V, IDSset= 0.8 A, f= 7.7, 8.1, 8.5 GHz,  $\Delta$ f= 5 MHz , Ta= +25 °C

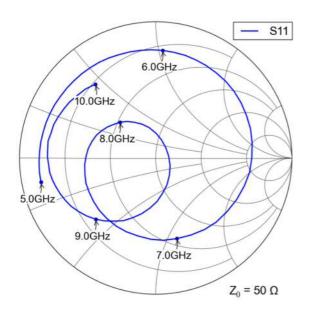


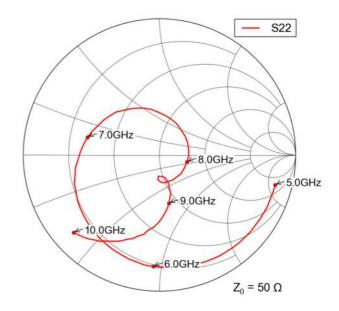


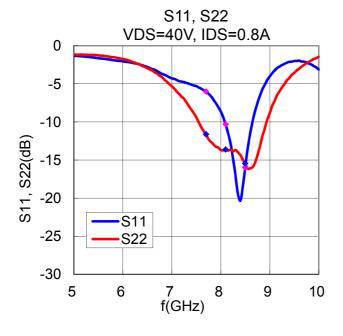


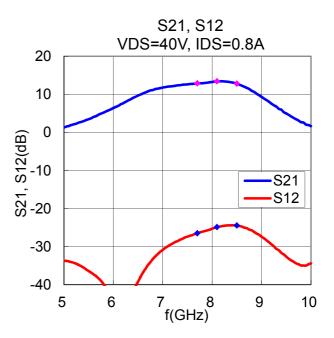
#### ·S-Parameters

VDS= 40 V, IDSset= 0.8 A, f= =5.0 to 10.0 GHz, Ta= +25  $^{\circ}$ C









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